



SILICON BIDIRECTIONAL DIACS

Part No.	Breakover Voltage	Breakover Current	Power Dissipation on Printed Circuit @T _a =50°C	Repetitive Peak on-state Current	Maximum Leakage Current	Rise Time
	V _{BO}	I _{BO}	P _c	I _{TRM}	I _B @25°C	Tr
	V	mA	mW	A	mA	ms

150mW / SILICON BIDIRECTIONAL / MINI MELF(GLASS) / Outline:52

LLDB3	28~36	100	150 ◆	2 ★	10 ▲	1.5
LLDB4	35~45	100	150 ◆	2 ★	10 ▲	1.5
LLDB6	56~70	100	150 ◆	1.6 ★	10 ▲	1.5
LLDC34	30~38	100	150 ◆	2 ★	10 ▲	1.5

T_j of -40°C to +110°C

T_{stg} of -40°C to +125°C

◆ at L=10mm

★ at t_p=10us and f=100Hz

▲ V_B=0.5V_Bmax.

150mW / SILICON BIDIRECTIONAL / DO-35(GLASS) / Outline:50

DB3	28~36	0.1	150 ◆	2 ★	0.01 ▲	1500
DB4	35~45	0.1	150 ◆	2 ★	0.01 ▲	1500
DB6	56~70	0.1	150 ◆	1.6 ★	0.01 ▲	1500
DC34	30~38	0.1	150 ◆	2 ★	0.01 ▲	1500

T_j of -40°C to +125°C

T_{stg} of -40°C to +125°C

◆ at L=10mm

★ at t_p=10us and f=100Hz

▲ V_B=0.5V_Bmax.